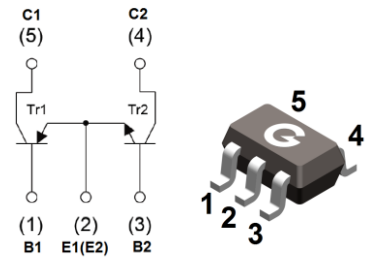


Features

- Includes a NPN and a PNP transistor in a package
- PNP and NPN transistors have common emitters
- Mounting cost and area can be cut in half

HF



SOT-353

Mechanical Data

- Case: SOT-353
- Molding compound: UL flammability classification rating 94V-0
- Terminals: Tin-plated; solderability per MIL-STD-202, Method 208

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
UMY1N	SOT-353	3000 pcs / Tape & Reel	Y1N

Maximum Ratings (@ T_A = 25°C unless otherwise specified)

Parameter	Symbol	NPN	PNP	Unit
Collector-Base Voltage	V _{CBO}	60	-60	V
Collector-Emitter Voltage	V _{CEO}	50	-50	V
Emitter-Base Voltage	V _{EBO}	7	-6	V
Collector Current (Continuous)	I _C	150	-150	mA
Collector Current (Peak)	I _{CM}	200	-200	mA

Thermal Characteristics

Parameter	Symbol	Value	Unit
Power Dissipation *1, 2	P _D	150	mW
Thermal Resistance Junction-to-Air *3	R _{θJA}	333	°C/W
Thermal Resistance Junction-to-Case *3	R _{θJC}	242	°C/W
Thermal Resistance Junction-to-Lead *3	R _{θJL}	259	°C/W
Operating Junction Temperature	T _J	-55 ~ +150	°C
Storage Temperature Range	T _{STG}	-55 ~ +150	°C

Notes:

- 120mW per element must not be exceeded
- Each terminal mount on a reference land
- The data tested by surface mounted on a 25.4mm * 25.4mm * 1mm FR4-epoxy P.C.B

Electrical Characteristics of NPN Transistor (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 50\mu\text{A}$, $I_E = 0$	60	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 1\text{mA}$, $I_B = 0$	50	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 50\mu\text{A}$, $I_C = 0$	7	-	-	V
Collector Cut-off Current	I_{CBO}	$V_{CB} = 60\text{V}$, $I_E = 0$	-	-	100	nA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 7\text{V}$, $I_C = 0$	-	-	100	nA
DC Current Gain	h_{FE}	$V_{CE} = 6\text{V}$, $I_C = 1\text{mA}$	120	-	560	-
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 50\text{mA}$, $I_B = 5\text{mA}$	-	-	0.4	V
Transition Frequency	f_T	$V_{CE} = 12\text{V}$, $I_E = -2\text{mA}$ $f = 100\text{MHz}$	-	180	-	MHz
Output Capacitance	C_{OBO}	$V_{CB} = 12\text{V}$, $f = 1.0\text{MHz}$, $I_E = 0$	-	-	3.5	pF

Electrical Characteristics of PNP Transistor (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -50\mu\text{A}$, $I_E = 0$	-60	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}$, $I_B = 0$	-50	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -50\mu\text{A}$, $I_C = 0$	-6	-	-	V
Collector Cut-off Current	I_{CBO}	$V_{CB} = -60\text{V}$, $I_E = 0$	-	-	-100	nA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -6\text{V}$, $I_C = 0$	-	-	-100	nA
DC Current Gain	h_{FE}	$V_{CE} = -6\text{V}$, $I_C = -1\text{mA}$	120	-	560	-
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -50\text{mA}$, $I_B = -5\text{mA}$	-	-	-0.5	V
Transition Frequency	f_T	$V_{CE} = -12\text{V}$, $I_E = 2\text{mA}$ $f = 100\text{MHz}$	-	140	-	MHz
Output Capacitance	C_{OBO}	$V_{CB} = -12\text{V}$, $f = 1.0\text{MHz}$, $I_E = 0$	-	-	5	pF

Ratings and Characteristic Curves-NPN (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

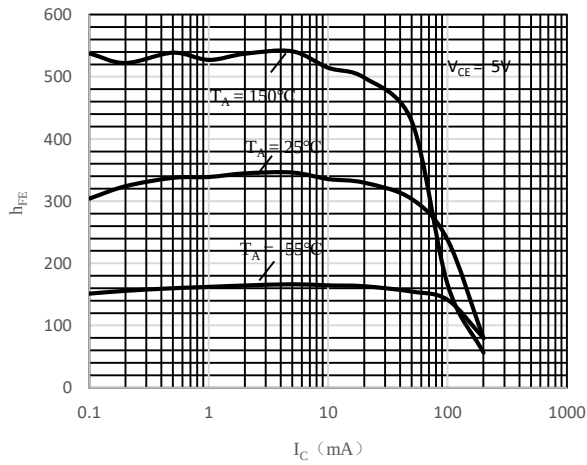


Fig 1 h_{FE} vs. I_C

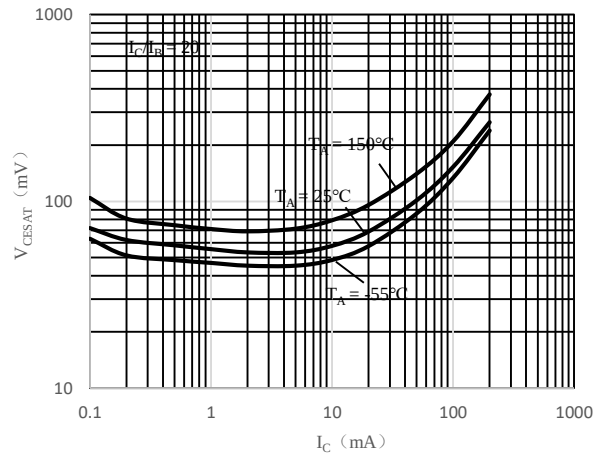


Fig 2 $V_{CE(sat)}$ vs. I_C

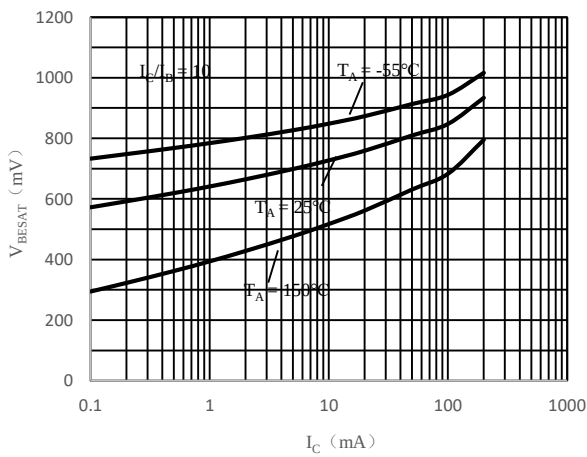


Fig 3 $V_{BE(sat)}$ vs. I_C

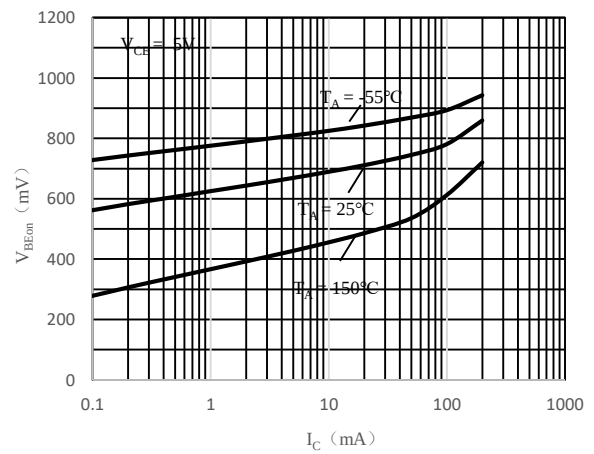


Fig 4 $V_{BE(on)}$ vs. I_C

Ratings and Characteristic Curves-PNP (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

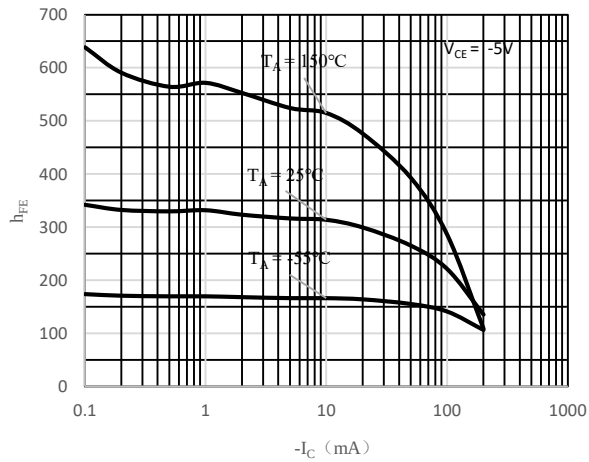


Fig 1 h_{FE} vs. I_C

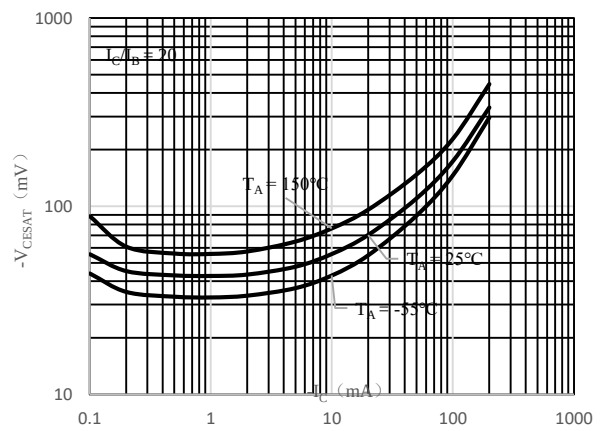


Fig 2 $V_{CE(sat)}$ vs. I_C

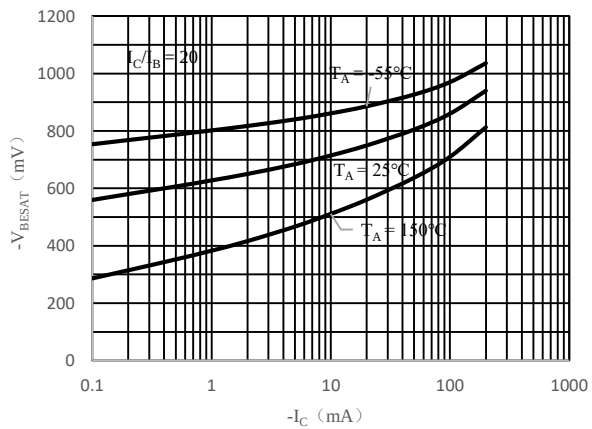


Fig 3 $V_{BE(sat)}$ vs. I_C

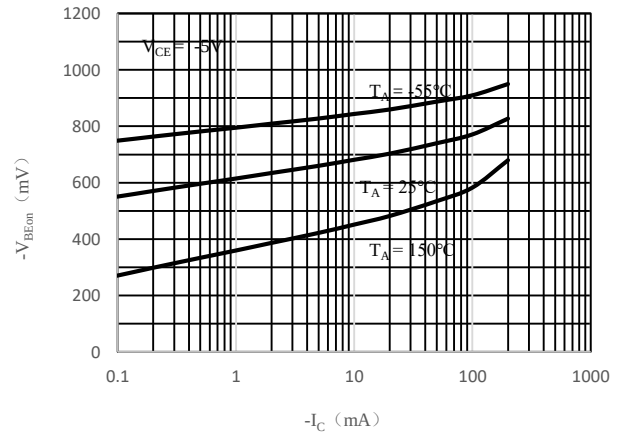
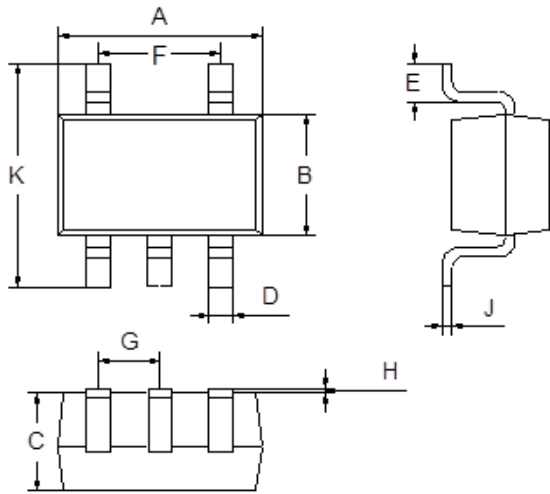


Fig 4 $V_{BE(on)}$ vs. I_C

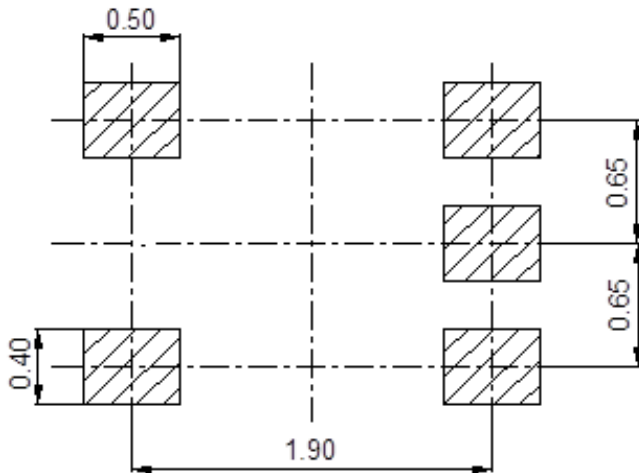
Package Outline Dimensions (Unit: mm)



SOT-353		
Dimension	Min.	Max.
A	2.00	2.20
B	1.15	1.35
C	0.85	1.05
D	0.15	0.35
E	0.25	0.40
F	1.20	1.40
G	0.60	0.70
H	0.02	0.10
J	0.05	0.15
K	2.20	2.40

Mounting Pad Layout (Unit: mm)

SOT-353



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